# Radiation Test-Bed for High Capacity Memory Components

# Final Presentation of ESTEC Contract No. 11356/95/NL/FM, CCN-7



**TU Braunschweig** 

Test-Bed Design Approach

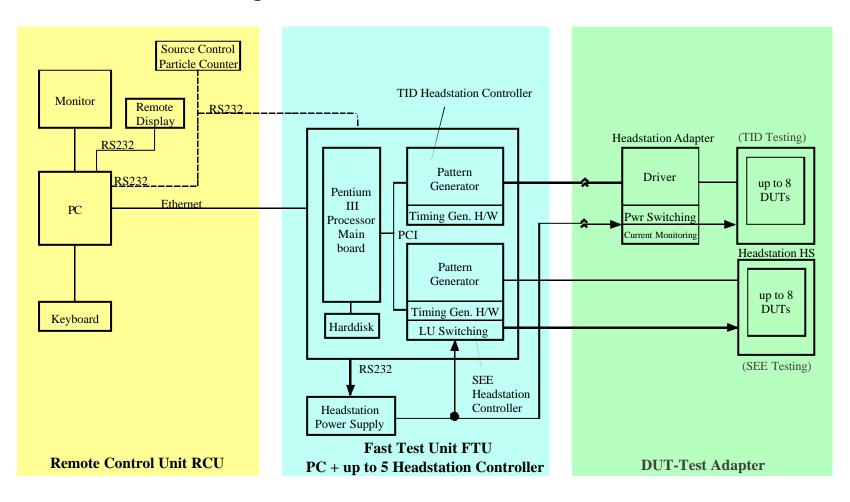
Test-Bed design mainly driven by three requirements:

- in situ testing
  - mandatory to detect and isolate special functional errors of state of the art devices, e.g. Flash Memories, FIFO's etc
- real time event detection and recording
  - supports isolation of special failure types, e.g. cluster errors (simultaneous multibit errors) or partial SEL
  - supports complete testing of large capacity devices within reasonable test time
- flexible and easily adaptable platform
  - more and more sophisticated "memory systems on a chip" are available and a test bed needs to be adaptable to these devices with special functions in a short time frame

**Derived Design Characteristics** 

- PC based System with special Plug-In Cards to implement real time functions (Fast Test Unit)
- TID and SEE Test capabilities and requirements achievable with the same basic equipment
- Adaptable Device Control and Test Patterns implemented in Firmware within configurable high performance FPGA's
- Remote control of in-situ tests supported via network
- Quick-Look data analysis to support in-situ tests

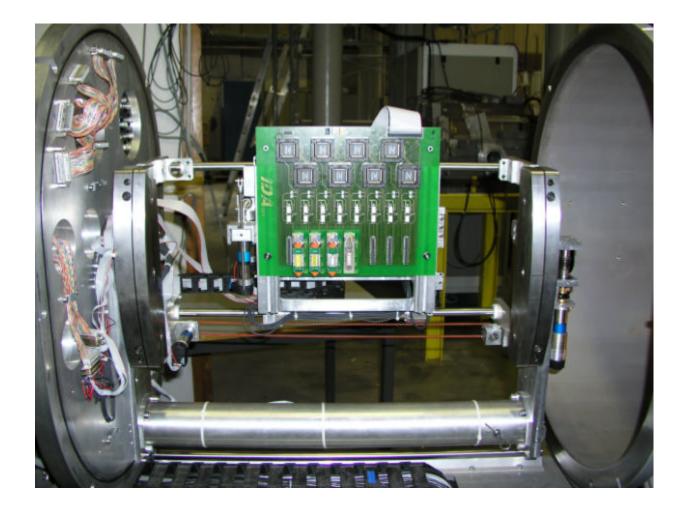
#### Block Diagram of In Situ Radiation Test Bed



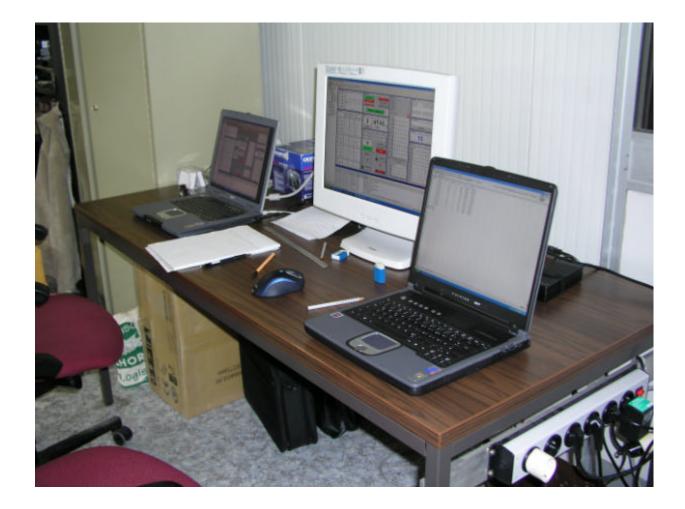
## Fast Test Unit



#### SEE Headstation with 4 DUT's



## Remote Control Unit



#### **Performance Characteristics**

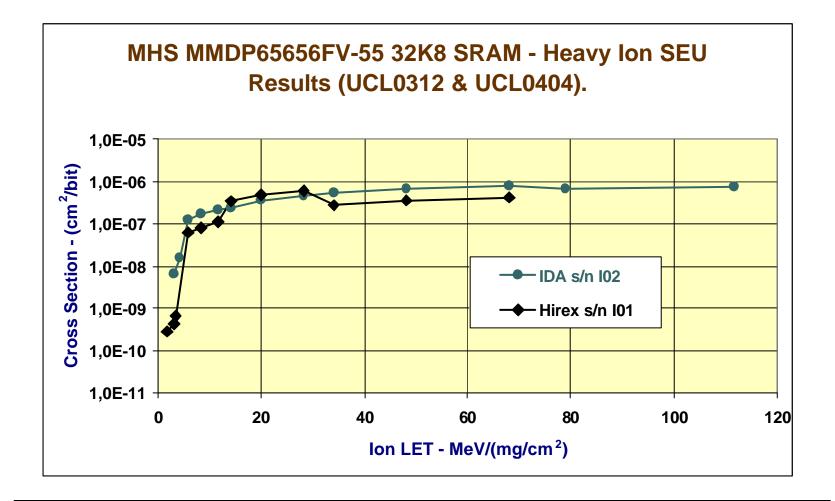
Address Pattern	Read Background, Write Background, Chessboard, Marching, MOVI,
Data Pattern	Constant (128 bit), Counting (64 bit), Pseudo-Random(64 bit),
Error Buffer	128k Error Records
Error Record Storage	limited to harddisk capacity
LU Detection	for both SEE-Test and TID-Tests, threshold adjustable
Current Measurement	1 mA resolution for SEE-Tests, 10µA resolution for TID-Tests
Devices	all kind of memory devices
Data Width	up to 16 Bit
Address Width	28 Bit static, 20 Bit (row) + 20 Bit (column) dynamic
Supply Voltage	2 – 6 Volts
Current	up to 200mA per device
Min. Cycle Time	currently 20 ns, 10ns in update version
Device Count	8 per Headstation, up to 4 Headstations connectable

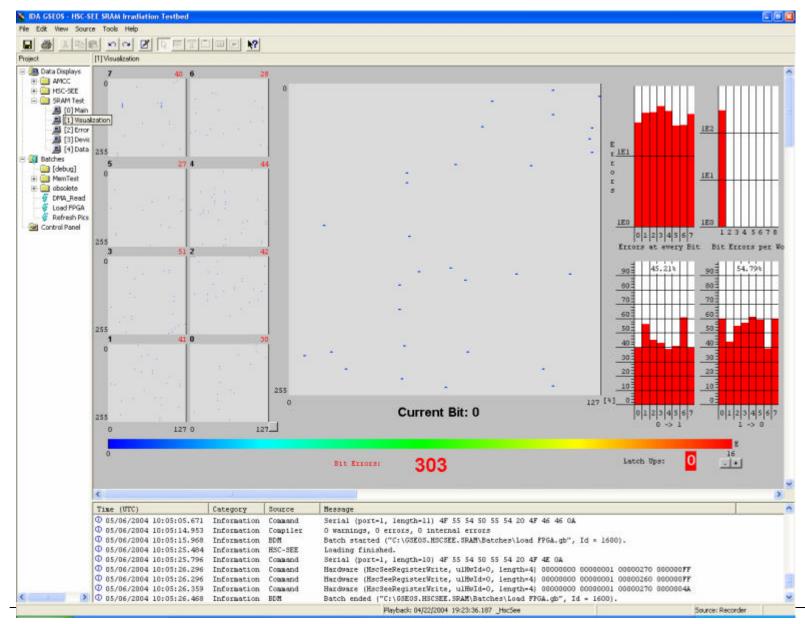
Distance Tester – Headstation1,5m (SEE-Tests), 5m (TID-Tests)Distance Tester – Operating PCup to 100m (standard ethernet)

**Test-Bed Verification** 

- Pre-Verification on System Level
  - a) with Laser Beam Test Set up (at IDA)
  - b) with Flash Memory Devices (at UCL)
- SEE-Test Verification on System Level
  SEE Testing of SRAM devices (at UCL)
- TID-Test Verification
  - TID Testing of SRAM devices (to be performed at ESTEC)

# SEE Test Results





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#### Summary

- Test Bed provides in-situ and real time SEE and TID Test capabilities for
  - Flash, SRAM (already implemented)
  - SDRAM, DDRAM (to be implemented soon)
  - Special devices (FIFO's, DPRAM's already implemented, others TBD)